TOSHIBA Diode Silicon Epitaxial Schottky Barrier Type

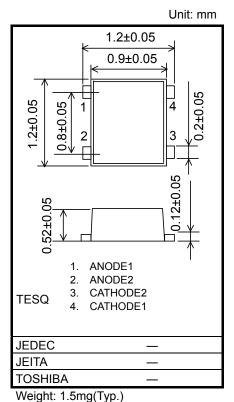
HN2S03T

High Speed Switching Application

- Two independent diodes are mounted on Thin Extreme Super Mini Quad package that are suitable for higher mounting densities.
- Low forward voltage : V_{F (3)} = 0.50V (typ.)
- Low reverse current : I_R= 0.5μA (max)
- Small total capacitance : C_T = 3.9pF (typ.)

Absolute Maximum Ratings (Q1, Q2 Common, Ta = 25°C)

Characteristic	Symbol	Rating	Unit	
Maximum (peak) reverse Voltage	V _{RM}	25	V	
Reverse voltage	V _R	20	V	
Maximum (peak) forward current	I _{FM}	100 *	mA	
Average forward current	Ι _Ο	50 *	mA	
Surge current (10ms)	I _{FSM}	1 *	А	
Power dissipation	Р	70 **	mW	
Junction temperature	Тј	125	°C	
Storage temperature range	T _{stg}	-55~125	°C	
Operating temperature range	T _{opr}	-40~100	°C	



Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

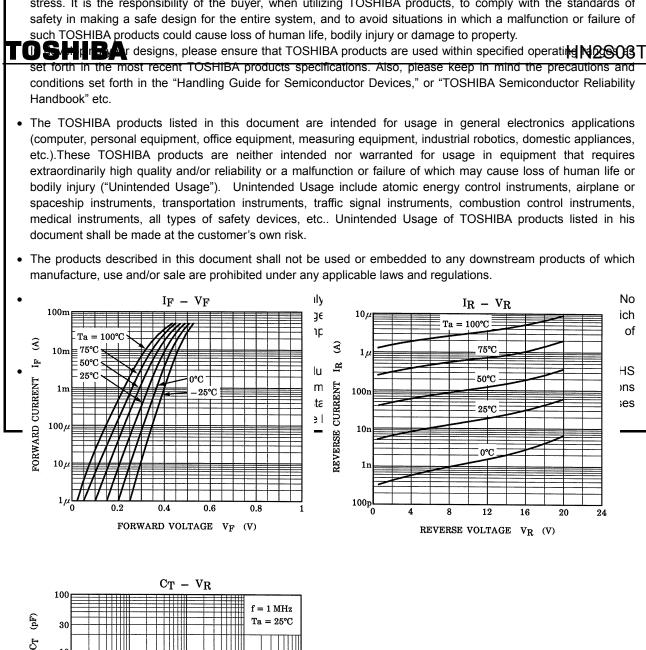
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

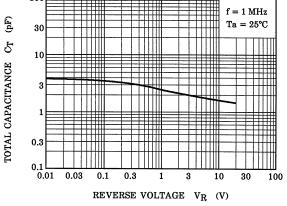
* : Unit rating. Total rating = Unit rating x 1.5

**: Total rating

Electrical Characteristics (Q1, Q2 Common, Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit	
Forward voltage	V _{F (1)}	_	I _F = 1mA		0.33			
	V _{F (2)}	—	I _F = 5mA		0.38		V	
	V _{F (3)}	_	I _F = 50mA	-	0.50	0.55		
Reverse current	Ι _R	_	V _R = 20V	-	_	0.5	μA	
Total capacitance	CT	_	V _R = 0, f = 1MH _z		3.9		pF	





Pin Assignment (Top View)



